

DATA SHEET

PHE13007

Silicon Diffused Power Transistor

Product specification

February 1999



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PHE13007

GENERAL DESCRIPTION

The PHE13007 is a silicon npn power switching transistor in the TO220AB envelope intended for use in high frequency electronic lighting ballast applications, converters, inverters, switching regulators, motor control systems, etc.

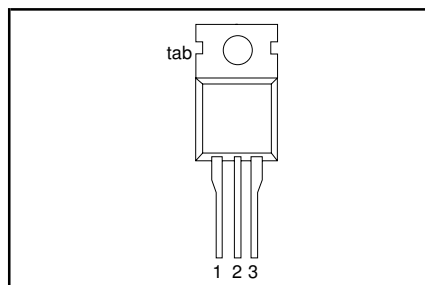
QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_{CESM}	Collector-emitter voltage peak value	$V_{BE} = 0\text{ V}$	-	700	V
V_{CBO}	Collector-Base voltage (open emitter)		-	700	V
V_{CEO}	Collector-emitter voltage (open base)		-	400	V
V_{EBO}	Emitter-Base voltage ($I_B = 0$)		-	9	V
I_C	Collector current (DC)		-	8	A
I_{CM}	Collector current peak value		-	16	A
P_{tot}	Total power dissipation	$T_{mb} \leq 25\text{ °C}$	-	80	W
V_{CEsat}	Collector-emitter saturation voltage	$I_C = 5.0\text{ A}; I_B = 1.0\text{ A}$	0.35	2.0	V
t_f	Fall time	$I_C = 5\text{ A}; I_{B1} = 1\text{ A}$	40	120	ns

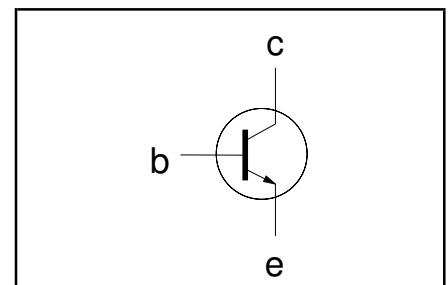
PINNING - TO220AB

PIN	DESCRIPTION
1	base
2	collector
3	emitter
tab	collector

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CESM}	Collector to emitter voltage	$V_{BE} = 0\text{ V}$	-	700	V
V_{CEO}	Collector to emitter voltage (open base)		-	400	V
V_{CBO}	Collector to base voltage (open emitter)		-	700	V
V_{EBO}	Emitter-Base voltage ($I_B = 0$)		-	9	V
I_C	Collector current (DC)		-	8	A
I_{CM}	Collector current peak value		-	16	A
I_B	Base current (DC)		-	4	A
I_{BM}	Base current peak value		-	8	A
P_{tot}	Total power dissipation	$T_{mb} \leq 25\text{ °C}$	-	80	W
T_{stg}	Storage temperature		-65	150	°C
T_j	Junction temperature		-	150	°C

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Junction to mounting base		-	1.56	K/W
$R_{th\ j-a}$	Junction to ambient	in free air	60	-	K/W

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STATIC CHARACTERISTICS $T_{mb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CES}	Collector cut-off current ¹	$V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$	-	-	0.2	mA
I_{CES}		$V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$ $T_j = 125\text{ }^{\circ}\text{C}$	-	-	1.0	mA
I_{EBO}	Emitter cut-off current	$V_{EB} = 9\text{ V}; I_C = 0\text{ A}$	-	-	1.0	mA
$V_{CEOsust}$	Collector-emitter sustaining voltage	$I_B = 0\text{ A}; I_C = 10\text{ mA};$ $L = 25\text{ mH}$	400	-	-	V
V_{CEsat}	Collector-emitter saturation voltage	$I_C = 2.0\text{ A}; I_B = 0.4\text{ A}$	-	0.15	1.0	V
V_{CEsat}		$I_C = 5.0\text{ A}; I_B = 1.0\text{ A}$	-	0.35	2.0	V
V_{CEsat}		$I_C = 5.0\text{ A}; I_B = 1.0\text{ A}$ ($T_C = 100\text{ }^{\circ}\text{C}$)	-	0.51	3.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C = 2.0\text{ A}; I_B = 0.4\text{ A}$	-	0.92	1.2	V
V_{BEsat}		$I_C = 5.0\text{ A}; I_B = 1.0\text{ A}$	-	1.05	1.6	V
V_{BEsat}		$I_C = 5.0\text{ A}; I_B = 1.0\text{ A}$ ($T_C = 100\text{ }^{\circ}\text{C}$)	-	1.00	1.5	V
h_{FE}	DC current gain	$I_C = 2.0\text{ A}; V_{CE} = 5\text{ V}$	8	17	40	
h_{FEsat}		$I_C = 5.0\text{ A}; V_{CE} = 5\text{ V}$	5	9	30	

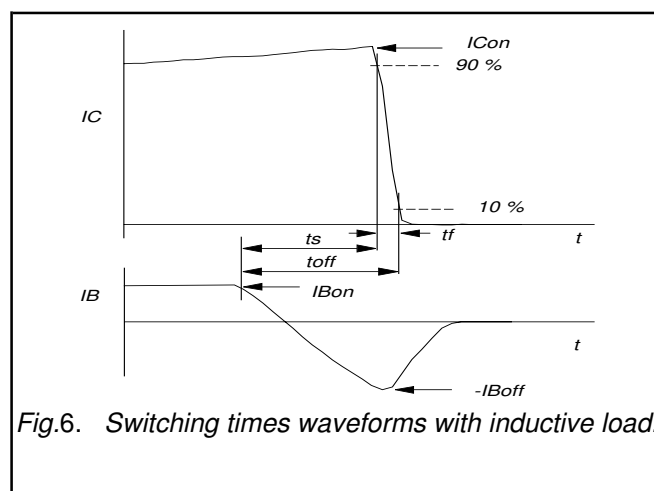
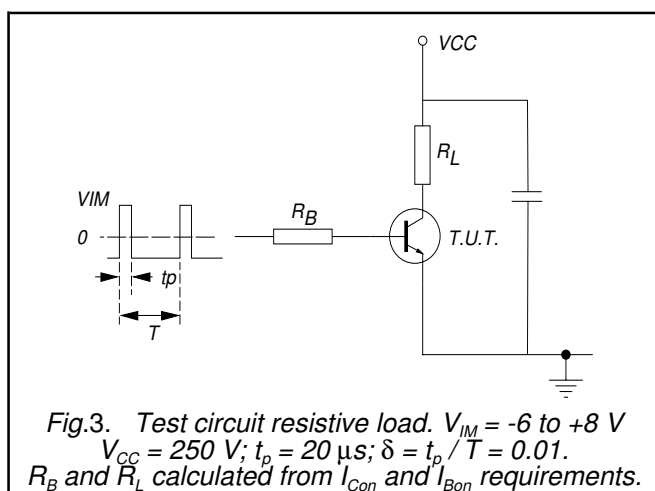
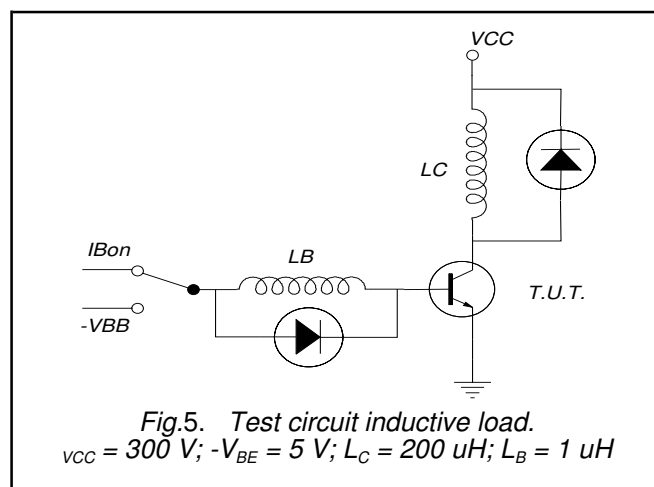
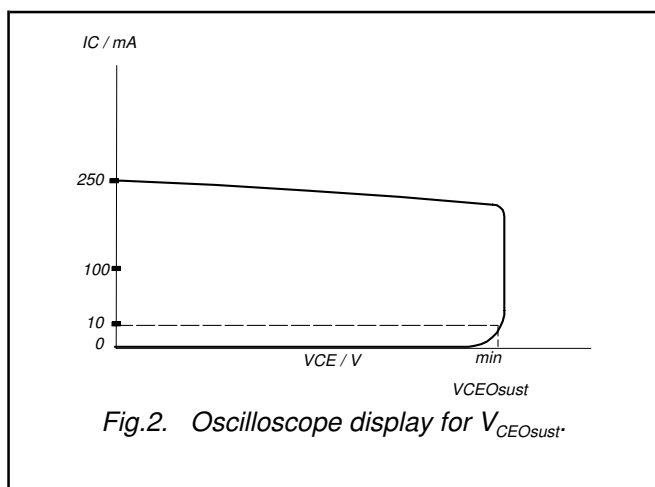
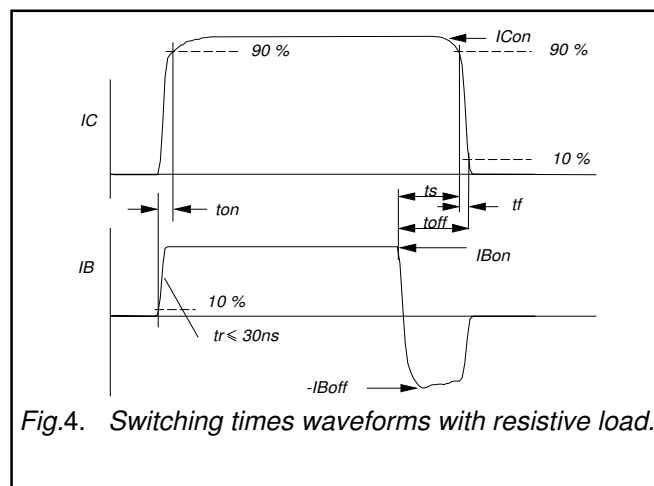
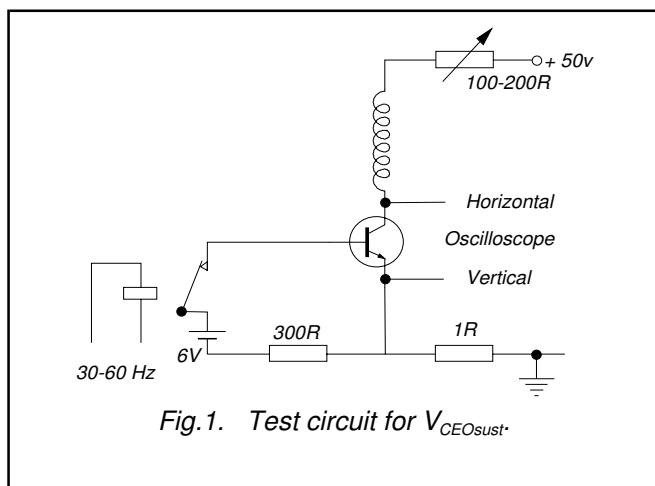
DYNAMIC CHARACTERISTICS $T_{mb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
	Switching times (resistive load)	$I_{Con} = 5\text{ A}; I_{Bon} = -I_{Boff} = 1\text{ A};$ $R_L = 75\text{ ohms}; V_{BB2} = 4\text{ V};$			
t_s	Turn-off storage time		1.8	3.0	μs
t_f	Turn-off fall time		0.3	0.7	μs
	Switching times (inductive load)	$I_{Con} = 5\text{ A}; I_{Bon} = 1\text{ A}; L_B = 1\text{ }\mu\text{H};$ $-V_{BB} = 5\text{ V}$			
t_s	Turn-off storage time		1.2	2.0	μs
t_f	Turn-off fall time		40	120	ns
	Switching times (inductive load)	$I_{Con} = 5\text{ A}; I_{Bon} = 1\text{ A}; L_B = 1\text{ }\mu\text{H};$ $-V_{BB} = 5\text{ V}; T_j = 100\text{ }^{\circ}\text{C}$			
t_s	Turn-off storage time		1.6	3.0	μs
t_f	Turn-off fall time		100	200	ns

¹ Measured with half sine-wave voltage (curve tracer).

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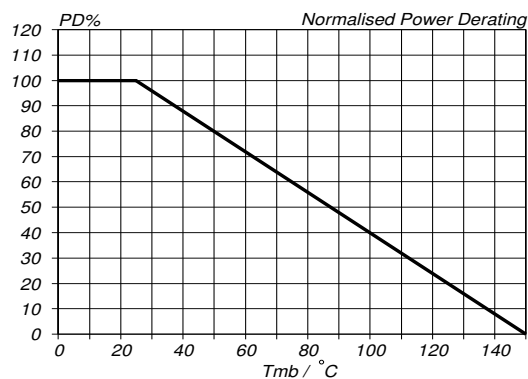


Fig. 7. Normalised power dissipation.
 $PD\% = 100 \cdot PD / PD_{25^\circ C} = f(T_{mb})$

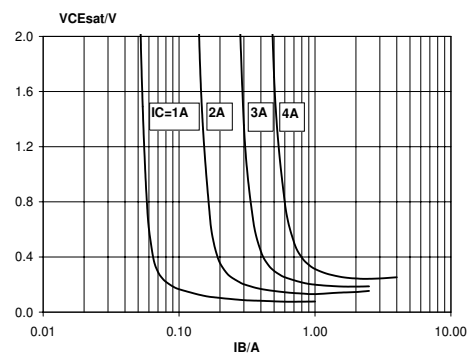


Fig. 10. Collector-Emitter saturation voltage.
 Solid lines = typ values, $V_{CEsat} = f(I_B)$; $T_j = 25^\circ C$.

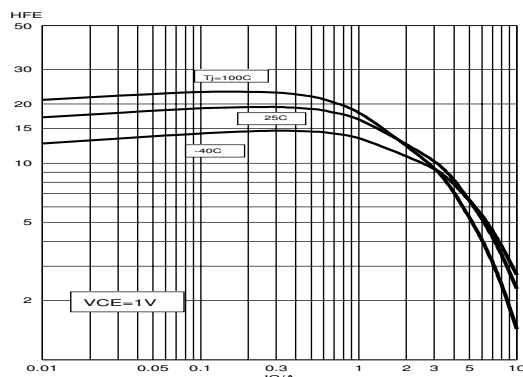


Fig. 8. Typical DC current gain. $h_{FE} = f(I_C)$
 parameter V_{CE}

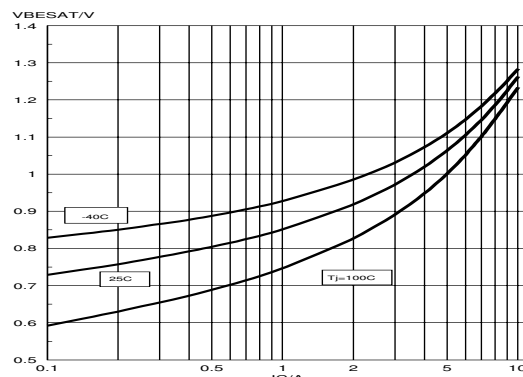


Fig. 11. Base-Emitter saturation voltage.
 Solid lines = typ values, $V_{BEsat} = f(I_C)$; at $I_C/I_B = 4$.

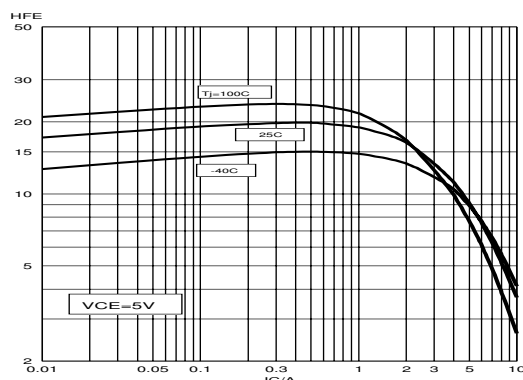


Fig. 9. Typical DC current gain. $h_{FE} = f(I_C)$
 parameter V_{CE}

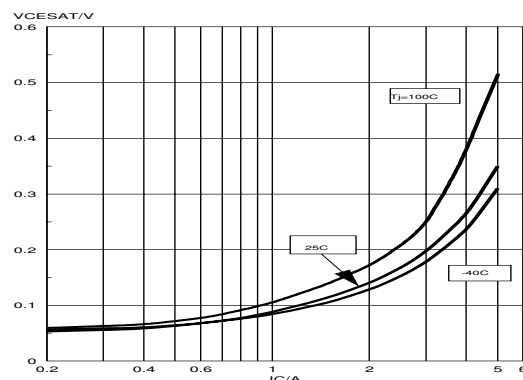


Fig. 12. Collector-Emitter saturation voltage.
 Solid lines = typ values, $V_{CEsat} = f(I_C)$; at $I_C/I_B = 4$.

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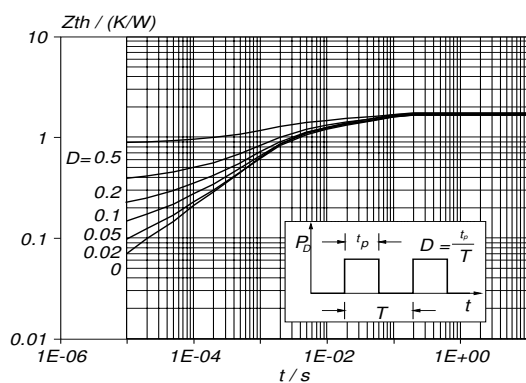


Fig. 13. Transient thermal impedance.
 $Z_{th\ j-mb} = f(t)$; parameter $D = t_p/T$

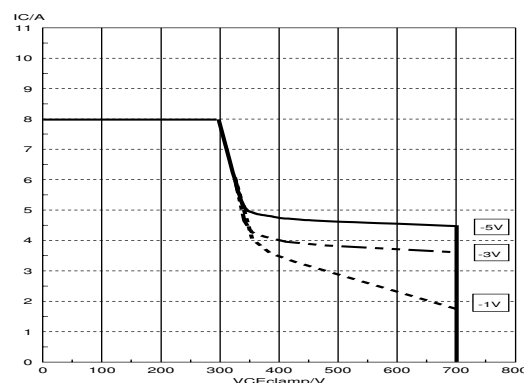


Fig. 15. Reverse bias safe operating area ($T_j < T_{jmax}$)
 for $-V_{BE} = 5V, 3V \text{ \& \ } 1V$.

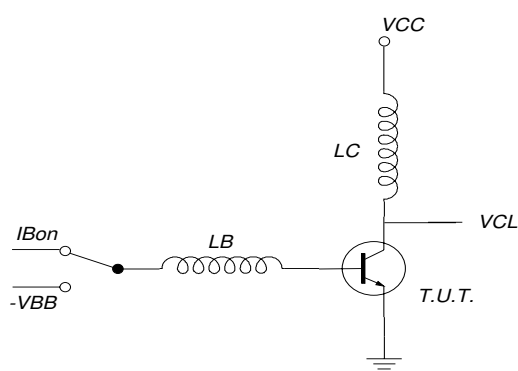


Fig. 14. Test circuit for reverse bias safe operating area.

$V_{clamp} < 700V$; $V_{cc} = 150V$; $-V_{be} = 5V, 3V \text{ \& \ } 1V$;
 $L_B = 1\mu H$; $L_C = 200\mu H$.

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MECHANICAL DATA

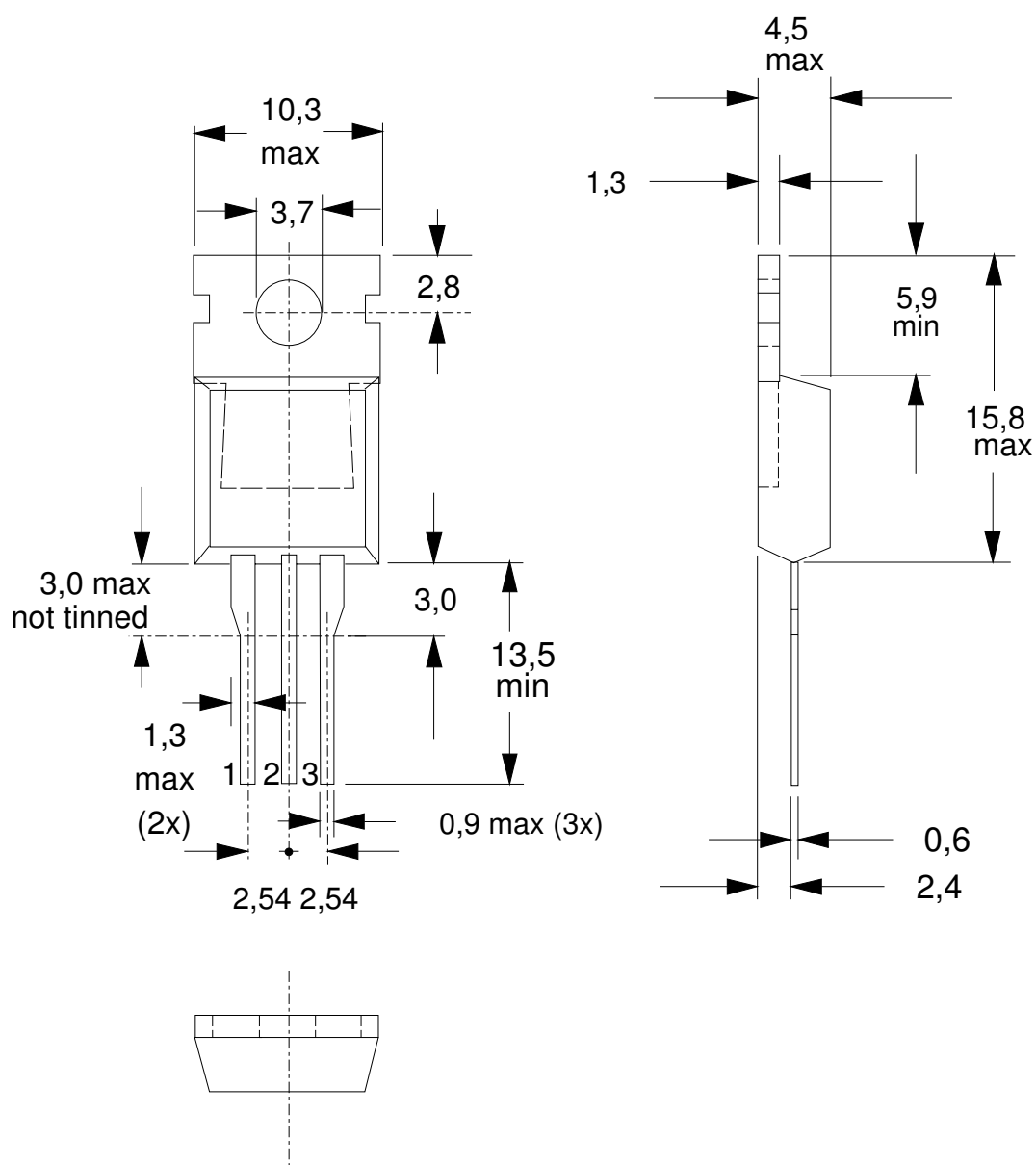
*Dimensions in mm**Net Mass: 2 g*

Fig.16. TO220AB; pin 2 connected to mounting base.

Notes

1. Refer to mounting instructions for TO220 envelopes.
2. Epoxy meets UL94 V0 at 1/8".